Abstract of Disclosure

A method of fabricating a semiconductor device includes the step of forming a source and a drain doped with a first conductivity type in an active area, which is made on both sides of a word line by an isolation layer of a second conductivity type doped substrate, each word line being separated by a predetermined interval; forming a first contact and a second contact by using the isolation layer which is separated at a wider interval on the source than on the drain to expose the source and the drain; and selectively implanting the second conductivity type dopant ion in the source by using the isolation layer and the word line as a ion implanting mask during a tilt ion implantation process.